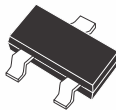


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**CMPT2484**  
**NPN SILICON**  
**LOW NOISE TRANSISTOR**



**SOT-23 CASE**

**Central**  
Semiconductor Corp.

**DESCRIPTION:**

The CENTRAL SEMICONDUCTOR CMPT2484 type is an NPN silicon low noise transistor manufactured by the epitaxial planar process, epoxy molded in a surface mount package, designed for low noise amplifier applications.

**Marking Code is C1U.**

**MAXIMUM RATINGS** ( $T_A=25^{\circ}\text{C}$ )

	<b>SYMBOL</b>		<b>UNITS</b>
Collector-Base Voltage	$V_{CBO}$	60	V
Collector-Emitter Voltage	$V_{CEO}$	60	V
Emitter-Base Voltage	$V_{EBO}$	6.0	V
Collector Current	$I_C$	50	mA
Power Dissipation	$P_D$	350	mW
Operating and Storage Junction Temperature	$T_J, T_{stg}$	-65 to +150	$^{\circ}\text{C}$
Thermal Resistance	$\theta_{JA}$	357	$^{\circ}\text{C}/\text{W}$

**ELECTRICAL CHARACTERISTICS** ( $T_A=25^{\circ}\text{C}$  unless otherwise noted)

<b>SYMBOL</b>	<b>TEST CONDITIONS</b>	<b>MIN</b>	<b>MAX</b>	<b>UNITS</b>
$I_{CBO}$	$V_{CB}=45\text{V}$		10	nA
$I_{CBO}$	$V_{CB}=45\text{V}, T_A=150^{\circ}\text{C}$		10	$\mu\text{A}$
$I_{EBO}$	$V_{EB}=5.0\text{V}$		10	nA
$BV_{CBO}$	$I_C=10\mu\text{A}$	60		V
$BV_{CEO}$	$I_C=10\text{mA}$	60		V
$BV_{EBO}$	$I_E=10\mu\text{A}$	5.0		V
$V_{CE(SAT)}$	$I_C=1.0\text{mA}, I_B=100\mu\text{A}$		0.35	V
$V_{BE(ON)}$	$V_{CE}=5.0\text{V}, I_C=1.0\text{mA}$		0.95	V
$h_{FE}$	$V_{CE}=5.0\text{V}, I_C=1.0\text{mA}$	250	---	
$h_{FE}$	$V_{CE}=5.0\text{V}, I_C=10\text{mA}$	---	800	
$C_{ob}$	$V_{CB}=5.0\text{V}, I_E=0, f=1.0\text{MHz}$		6.0	pF
	$V_{EB}=0.5\text{V}, I_C=0, f=1.0\text{MHz}$		6.0	pF
	$V_{CE}=5.0\text{V}, I_C=10\mu\text{A}, R_S=10\text{k}\Omega$ $f=1.0\text{kHz}, BW=200\text{Hz}$		3.0	dB



All dimensions in inches (mm).

